

Hyperfast Rectifier, 3 A FRED Pt[®]


SMC (DO-214AB)

FEATURES

- Hyperfast recovery time, reduced Q_{rr} , and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
 COMPLIANT
 HALOGEN
FREE
DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element.

PRODUCT SUMMARY	
Package	SMC (DO-214AB)
$I_{F(AV)}$	3 A
V_R	100 V
V_F at I_F	0.69 V
t_{rr}	25 ns
T_J max.	175 °C
Diode variation	Single die

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		100	V
Average rectified forward current	$I_{F(AV)}$	$T_{Sp} = 142$ °C	3	A
Non-repetitive peak surge current	I_{FSM}	$T_J = 25$ °C, 6 ms square pulse	130	
Operating junction and storage temperatures	T_J, T_{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	$I_R = 100$ μ A	100	-	-	V
Forward voltage, per diode	V_F	$I_F = 3$ A	-	0.83	0.90	
		$I_F = 3$ A, $T_J = 125$ °C	-	0.69	0.75	
Reverse leakage current, per diode	I_R	$V_R = V_R$ rated	-	-	2	μ A
		$T_J = 125$ °C, $V_R = V_R$ rated	-	1	10	
Junction capacitance	C_T	$V_R = 100$ V	-	23	-	pF



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time	t _{rr}	I _F = 1 A, di _F /dt = 50 A/μs, V _R = 30 V	-	27	-	ns	
		I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A	-	-	25		
		T _J = 25 °C	-	18	-		
		T _J = 125 °C	-	30	-		
Peak recovery current	I _{RRM}	I _F = 3 A, di _F /dt = 200 A/μs, V _R = 160 V	T _J = 25 °C	-	2.1	-	A
			T _J = 125 °C	-	4	-	
Reverse recovery charge	Q _{rr}		T _J = 25 °C	-	19	-	nC
			T _J = 125 °C	-	60	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to case	R _{thJC}	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	7.7	14	°C/W
Approximate weight			0.24			g
			0.008			oz.
Marking device		Case style SMC (DO-214AB)	3H1			

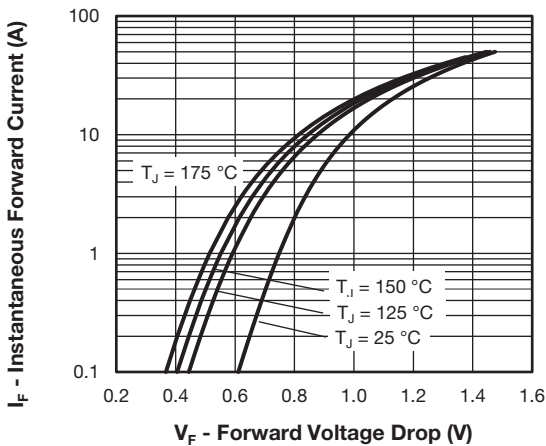


Fig. 1 - Typical Forward Voltage Drop Characteristics

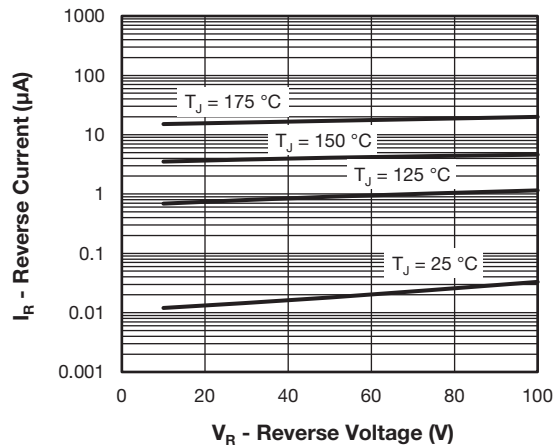


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

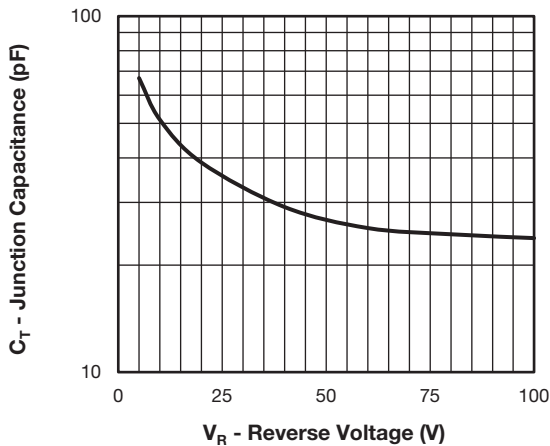


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

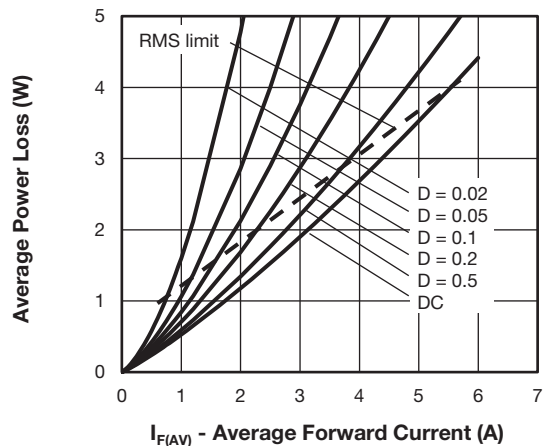


Fig. 5 - Forward Power Loss Characteristics

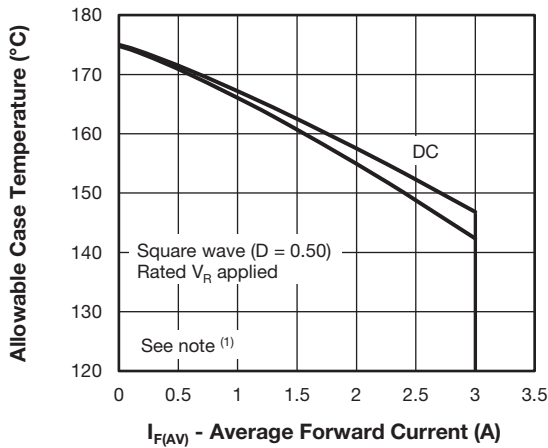


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

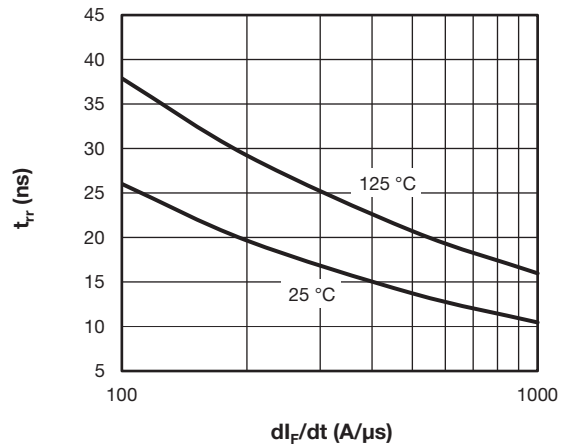


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

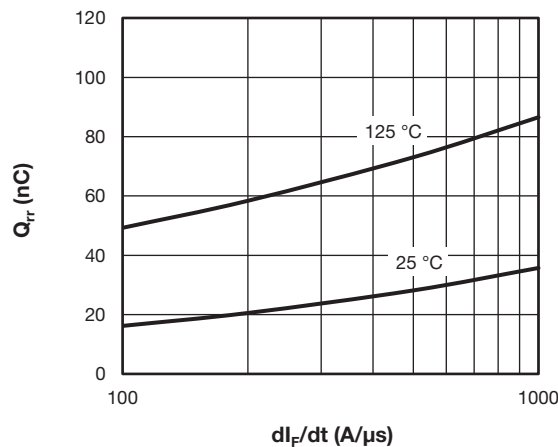
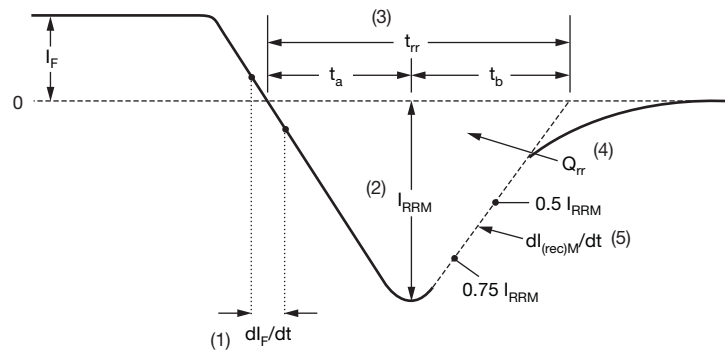


Fig. 7 - Typical Stored Charge vs. dI_F/dt

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$;
- P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5);
- P_{dREV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R



- (1) di_F/dt - rate of change of current through zero crossing
- (2) I_{RRM} - peak reverse recovery current
- (3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}
- (5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code	VS-	3	E	C	H	01	-M3
	①	②	③	④	⑤	⑥	⑦

- 1** - Vishay Semiconductors product
- 2** - Current code (3 = 3 A)
- 3** - Circuit configuration:
E = single diode
- 4** - C = SMC package
- 5** - Process type,
H = hyperfast recovery
- 6** - Voltage code (01 = 100 V)
- 7** - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-3ECH01-M3/9AT	3500	3500	13" diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95402
Part marking information	www.vishay.com/doc?95472
Packaging information	www.vishay.com/doc?95404